

NXP multi-channel ESD protection and EMI filter IP425xCZ8-4/CZ12-6/CZ16-8 IP4256CZ3-M/CZ5-W/CZ6-F

30 dB EMI filter with up to 30 kV IEC contact ESD protection in leadless packages

These highly integrated, space-saving devices, housed in NXP's Ultra Thin Leadless Plastic (ULTP) package, combine high-level ESD protection with EMI filtering of all relevant 2G and 3G mobilephone, WLAN and Bluetooth frequencies. The ESD protection exceeds the requirements of the IEC 61000-4-2 level 4 standard. NXP has 1.000 shot-proven ESD solutions that protect all kinds of portable applications over their full lifetimes, and provides a complete in-house production flow for added supply reliability.

Key features of new family

- Up to 30 dB insertion loss at mobile-phone frequencies (800 MHz to 3 GHz)
- ▶ High ESD protection exceeding IEC 61000-4-2 level 4
- Available as 1-, 2-, 4-, 6- or 8-channel filter
- Dark Green-compliant (RoHS-compliant and halogen-/ antimony-free)
- ▶ Ultra-thin leadless package, less than 0.5 mm height
- Terminal pitch of 0.4 mm

Key benefits

- Easy routing

Key applications

EMI/RFI filtering and downstream ESD protection in mobile and portable applications

- ▶ Camera interface
- Display and LCD interface
- Memory card interface (SD, MMC, etc.)
- ▶ Touch or keypad interface
- Bottom connector



EMI filter family in plastic packages

	IP4251CZ16-8 /CZ12-6/CZ8-4	IP4252CZ16-8 /CZ12-6/CZ8-4	IP4253CZ16-8 /CZ12-6/CZ8-4	IP4254CZ16-8 /CZ12-6/CZ8-4	IP4256CZ3-M	IP4256CZ5-W	IP4256CZ6-F
Package	UTLP SOT983/984/985	UTLP SOT983/984/985	UTLP SOT983/984/985	UTLP SOT983/984/985	SOT883	SOT665	SOT886
No. of channels	4, 6, 8	4, 6, 8	4, 6, 8	4, 6, 8	1	2	2
Width (mm)	1.35	1.35	1.35	1.35	0.6	1.2	1
Length (mm)	1.7, 2.5, 3.3	1.7, 2.5, 3.3	1.7, 2.5, 3.3	1.7, 2.5, 3.3	1	1.6	1.45
Max. height (mm)	0.5	0.5	0.5	0.5	0.5	0.6	0.5
Channel resistance (Ω , typ)	100	40	200	100	100	100	100
Line capacitance (pF @ 0.0 V, typ.)	15	18	45	45	30	30	30
Line capacitance (pF @ 2.5 V, typ.)	10	12	30	30	19	19	19
ESD IEC61000-4-2 (kV contact, typ.)	15	15	30	30	25	25	25
Robustness at ESD level 4 (1000 shots, IEC61000-4-2)	yes	yes	yes	yes	yes	yes	yes

Clamping voltage of IP4254CZ16-8 at ±8 kV IEC 61000-4-2, level 4 pulse

 Integrated π-filter (C-R-C) structure assures excellent ESD pulse transient response



Application example

4-channel integrated EMI filter with ESD protection

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Why integrated silicon solutions?

- No degradation full ESD protection even after 1000 IEC level strikes
- Predictable, reliable suppression of relevant 2G and 3G mobile-phone frequencies while minimizing signal loss
- Very low clamping voltage due to optimized π-filter structures (C-R-C structure)
 - Prevent damage of ESD-sensitive circuits during an ESD event (IEC testing only ensures the device will survive)

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- Protect against soft errors caused by non-destructive transients
- Protect sensitive system chips

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